1. General description

NPN/NPN high power double bipolar transistor in a SOT1205 (LFPAK56D) Surface-Mounted Device (SMD) power plastic package.

PNP/PNP complement: PHPT610030PK.

NPN/PNP complement: PHPT610030NPK.

2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- Motor control
- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Relay replacement

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V _{CEO}	collector-emitter voltage	open base		-	-	100	V
I _C	collector current			-	-	3	Α
Per transistor							,
R _{CEsat}	collector-emitter saturation resistance	I_C = 3 A; I_B = 0.3 A; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C		-	75	110	mΩ





5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	E1	emitter TR1	8 7 6 5 □ □ □ □	C1 B2 E2	
2	B1	base TR1	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	Pr Pr	
3	E2	emitter TR2		(TR1)	
4	B2	base TR2		E1	
5	C2	collector TR2			-
6	C2	collector TR2		sym140	
7	C1	collector TR1	1 2 3 4 LFPAK56D (SOT1205)		
8	C1	collector TR1	21174(005 (0011200)		

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PHPT610030NK	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205			

7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT610030NK	10030NK

8. Limiting values

Table 5. Limiting values

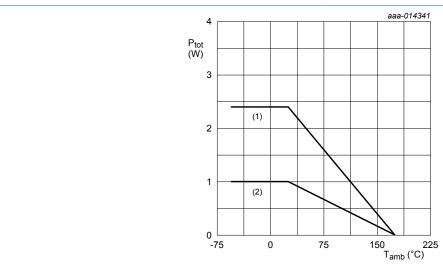
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transistor					
V _{CBO}	collector-base voltage	open emitter	-	100	V
V _{CEO}	collector-emitter voltage	open base	-	100	V
V _{EBO}	emitter-base voltage	open collector	-	7	V
I _C	collector current		-	3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	8	Α
I _B	base current		-	0.5	Α

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Symbol	Parameter	Conditions		Min	Max	Unit
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1	W
			[2]	-	2.4	W
			[3]	-	25	W
Per device						,
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.25	W
			[4]	-	5	W
			[2]	-	3	W
Tj	junction temperature			-	175	°C
T _{stg}	storage temperature			-65	175	°C
T _{amb}	ambient temperature			-55	175	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Power dissipation from junction to mounting base.
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, standard footprint

Fig. 1. Per transistor: power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	r						
R _{th(j-a)}	thermal resistance	in free air [1	[1]	-	-	150	K/W
from junction to ambient	C	[2]	-	-	62.5	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	6	K/W
Per device							
R _{th(j-a)}	thermal resistance	in free air	[1]	-	-	120	K/W
from junction to ambient	-		[2]	-	-	50	K/W
		[3]	-	-	30	K/W	

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

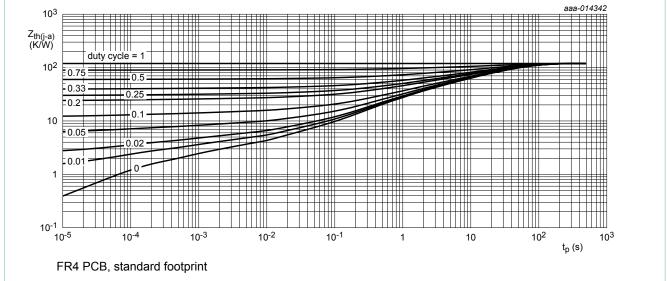


Fig. 2. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

NPN/NPN high power double bipolar transistor

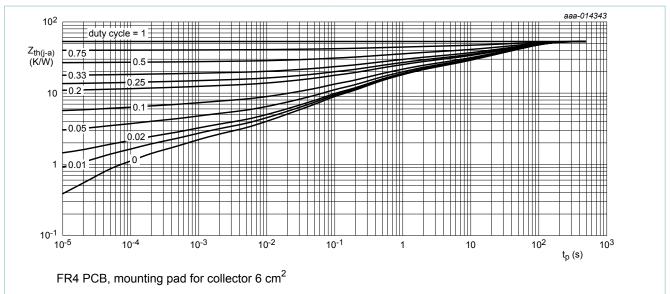


Fig. 3. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

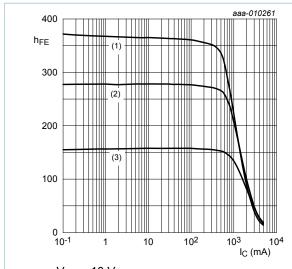
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor		'			,
I _{CBO}	collector-base cut-off	V _{CB} = 80 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 80 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 80 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 7 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 10 V; I_{C} = 500 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \bar{o} \le 0.02; \ T_{amb}$ = 25 °C	150	250	-	
		V_{CE} = 10 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	80	250	-	
		V_{CE} = 10 V; I_{C} = 2 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	20	100	-	
		V_{CE} = 10 V; I_{C} = 3 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	10	40	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = 1 A; I_{B} = 50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	90	150	mV
		I_{C} = 3 A; I_{B} = 300 mA; pulsed; $t_{p} \le$ 300 µs; $\bar{o} \le$ 0.02; T_{amb} = 25 °C	-	225	330	mV

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{CEsat}	collector-emitter saturation resistance	I_C = 3 A; I_B = 0.3 A; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	75	110	mΩ
V_{BEsat}	base-emitter saturation voltage	I_{C} = 1 A; I_{B} = 50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	0.86	1	V
		I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02; T_{amb} = 25 °C	-	1	1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 0.1 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	0.67	0.85	V
t _d	delay time	V_{CC} = 12.5 V; I_{C} = 1 A; I_{Bon} = 50 mA; I_{Boff} = -50 mA; T_{amb} = 25 °C	-	20	-	ns
t _r	rise time		-	300	-	ns
t _{on}	turn-on time		-	320	-	ns
t _s	storage time		-	830	-	ns
t _f	fall time		-	470	-	ns
t _{off}	turn-off time		-	1300	-	ns
f⊤	transition frequency	V_{CE} = 10 V; I_{C} = 100 mA; f = 100 MHz; T_{amb} = 25 °C	-	140	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	11	-	pF



 V_{CE} = 10 V

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) T_{amb} = 25 °C

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 4. DC current gain as a function of collector current; typical values

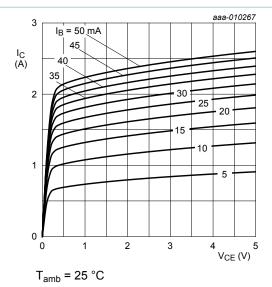
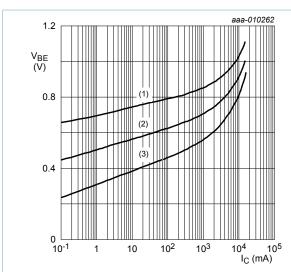


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



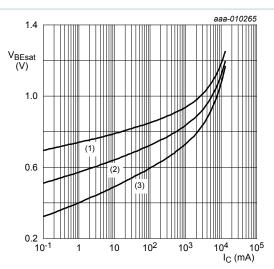
$$V_{CE} = 2 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = 100 °C

Fig. 6. Base-emitter voltage as a function of collector current; typical values



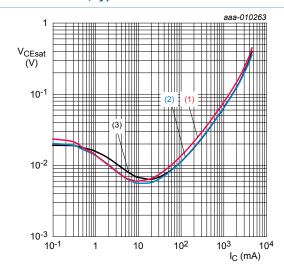
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



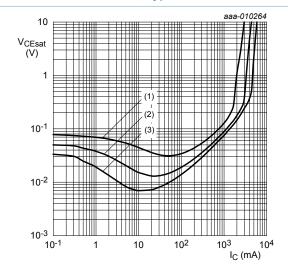
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

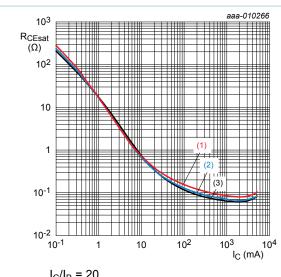
(1)
$$I_C/I_B = 50$$

(2)
$$I_C/I_B = 20$$

(3)
$$I_C/I_B = 10$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

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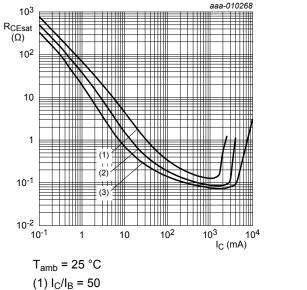
$$I_C/I_B = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



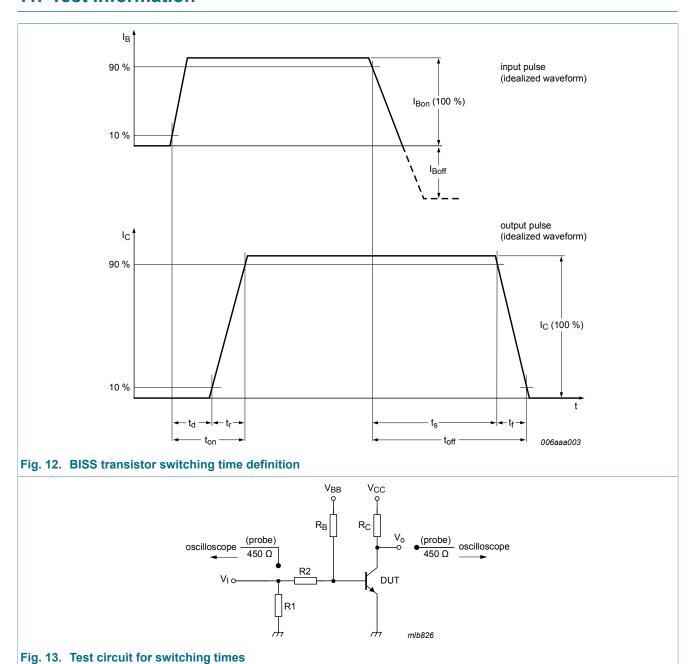
(1)
$$I_C/I_B = 5$$

(2)
$$I_C/I_B = 20$$

(3)
$$I_C/I_B = 10$$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

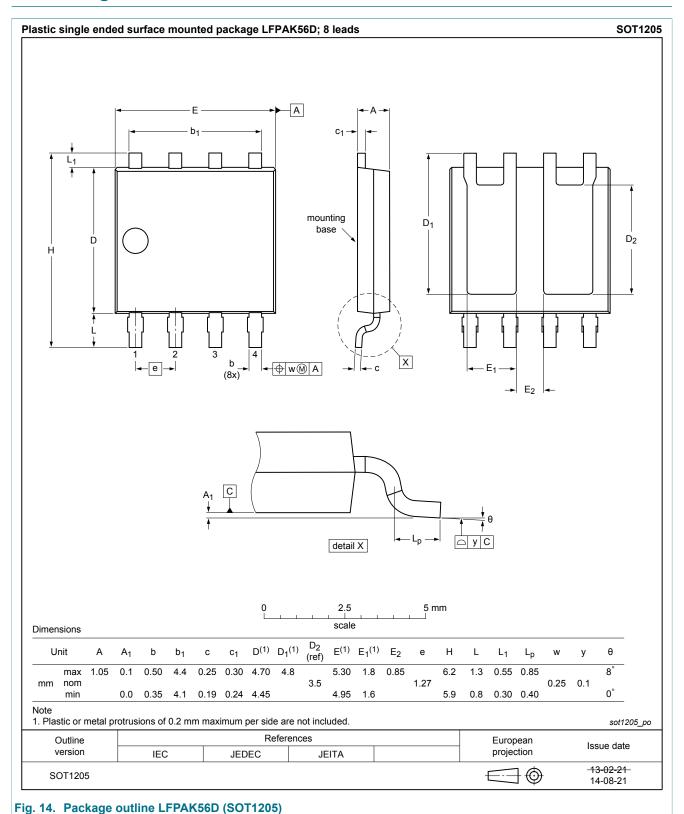
11. Test information



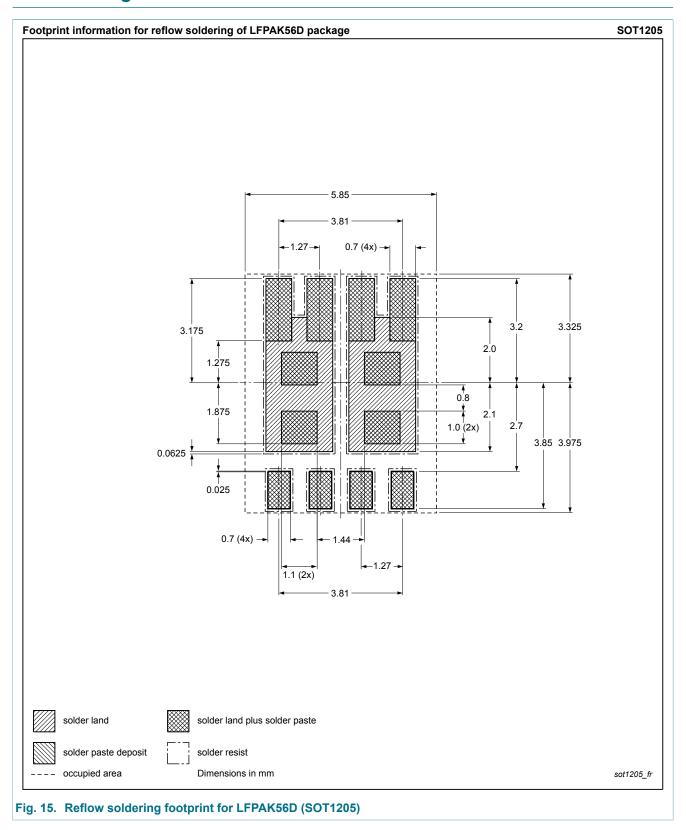
11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



13. Soldering



PHPT610030NK

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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT610030NK v.1	20141020	Product data sheet	-	-

NPN/NPN high power double bipolar transistor

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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NPN/NPN high power double bipolar transistor

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